

BRS S1	2	20040207412	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:29
BRS S2	487	324/658.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	6/1/2005 10:18
BRS S3	304	324/686.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 14:58
BRS S4	9	6300765	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:44
BRS S5	20	5999010	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 14:20
BRS S6	220	324/679.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 15:45
BRS S7	514	324/663.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 15:45
BRS S8	5183	(324/158.1).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 15:45
BRS S9	311	S8 and (capacit\$5 with measur\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 16:01
BRS S10	178	S9 and (current with (measur\$5 OR detect\$5 or meter\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 15:58
BRS S11	71	S10 and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 15:58
BRS S12	326	S7 and (capacit\$5 with measur\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 15:58
BRS S13	163	S12 and (current with (measur\$5 OR detect\$5 or meter\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 16:02
BRS S14	34	S13 and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 16:02
BRS S15	504	324/658.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 16:01
BRS S16	338	S15 and (capacit\$5 with measur\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 16:01
BRS S17	145	S16 and (current with (measur\$5 OR detect\$5 or meter\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/28/2005 16:02
BRS S18	48	S17 and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:37
BRS S28	504	324/658.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:37
BRS S29	338	S28 and (capacit\$5 with measur\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:37
BRS S30	145	S29 and (current with (measur\$5 OR detect\$5 or meter\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:37
BRS S31	48	S30 and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:52
BRS S32	13	S31 and leak\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:37
BRS S33	9	6300765	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:45
BRS S34	3	S33 and leak\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:44
BRS S35	20	5999010	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:45
BRS S36	5	S35 and leak\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 8:45
BRS S38	21	324/769.ccls. and ("SOI" or (silicon near2 insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 11:08
BRS S39	8	324/766.ccls. and ("SOI" or (silicon near2 insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:39
BRS S40	5	324/758.ccls. and ("SOI" or (silicon near2 insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:37
BRS S41	14	324/763.ccls. and ("SOI" or (silicon near2 insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:40
BRS S42	33	(324/158.1).ccls. and ("SOI" or (silicon near2 insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:40
BRS S43	1	324/686.ccls. and ("SOI" or (silicon near2 insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:41
BRS S44	1	324/679.ccls. and ("SOI" or (silicon near2 insulator))	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:41
BRS S45	47	(S38 S39 S40 S41 S42 S43) and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 9:52
BRS S46	68	(324/763.ccls. 324/766.ccls. 324/686.ccls. 324/769.ccls.) and ((contact or connect\$3) near3 hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 11:12
BRS S47	40	S46 and capacit\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	10/31/2005 11:15